

# Switching Diode

## ● Applications

Ultra high speed switching

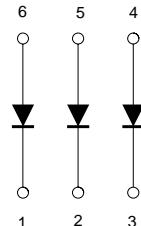
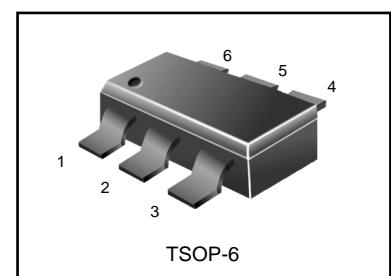
## ● Features

- 1) Multiple diodes in one small surface mount package.
- 2) Diode characteristics are matched in the package.
- 3) Pb-Free Package is Available.
- 4) S- Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

## ● Construction

Silicon epitaxial planar

**LIMN10T1G  
S-LIMN10T1G**



## ● Device Marking Ordering Information

| Device                   | Marking | Shipping        |
|--------------------------|---------|-----------------|
| LIMN10T1G<br>S-LIMN10T1G | N10     | 3000 Tape&Reel  |
| LIMN10T3G<br>S-LIMN10T3G | N10     | 10000 Tape&Reel |

## ● Absolute maximum ratings (Ta=25°C)

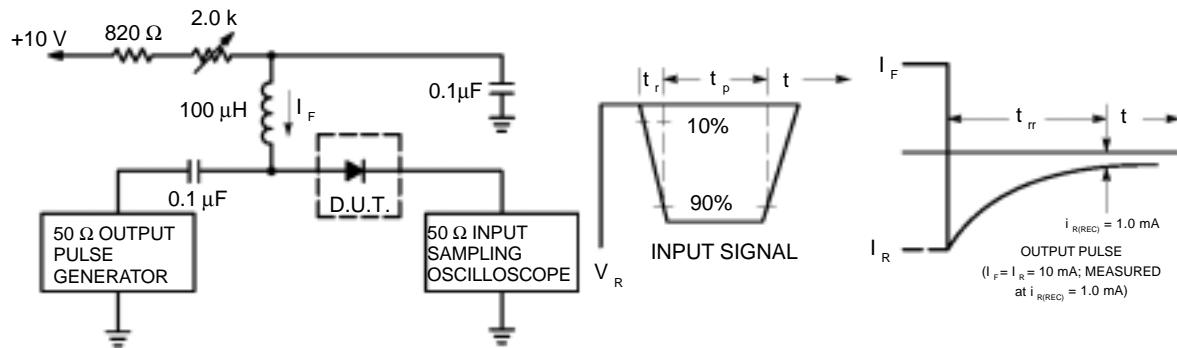
| Parameter                 | Symbol             | Limits      | Unit |
|---------------------------|--------------------|-------------|------|
| Peak reverse voltage      | V <sub>RM</sub>    | 80          | V    |
| DC reverse voltage        | V <sub>R</sub>     | 80          | V    |
| Peak forward current      | I <sub>FM</sub>    | 300         | mA   |
| Mean rectifying current   | I <sub>O</sub>     | 100         | mA   |
| Surge current (1us)       | I <sub>surge</sub> | 4           | A    |
| Power dissipation (total) | P <sub>d</sub>     | 300 *1      | mW   |
| Junction temperature      | T <sub>j</sub>     | 150         | °C   |
| Storage temperature       | T <sub>sg</sub>    | - 55 ~ +150 | °C   |

\*1 Not to exceed 200mW per element.

## ● Electrical characteristics (Ta=25°C)

| Parameter                     | Symbol          | Min. | Typ. | Max. | Unit | Conditions                               |
|-------------------------------|-----------------|------|------|------|------|--|
| Forward voltage               | V <sub>F</sub>  | —    | —    | 1.2  | V    | I <sub>F</sub> =100mA                    |
| Reverse current               | I <sub>R</sub>  | —    | —    | 0.1  | μA   | V <sub>R</sub> =70V                      |
| Capacitance between terminals | C <sub>T</sub>  | —    | —    | 3.5  | pF   | V <sub>R</sub> =6V , f=1MHz              |
| Reverse recovery time         | t <sub>rr</sub> | —    | —    | 4    | ns   | V <sub>R</sub> =6V , I <sub>F</sub> =5mA |

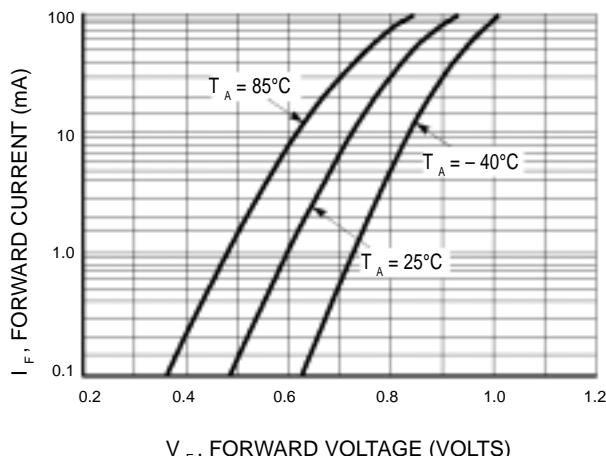
# LIMN10T1G, S-LIMN10T1G



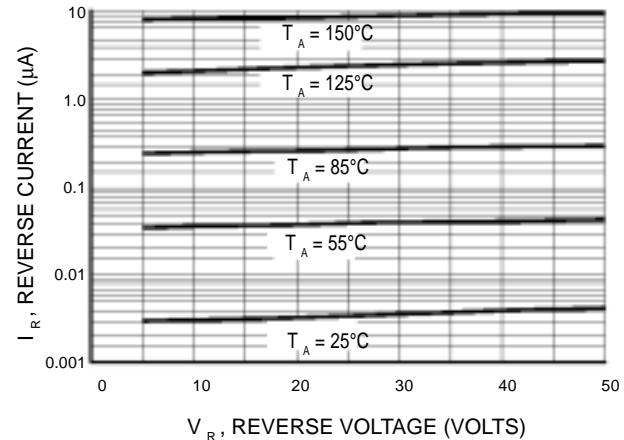
- Notes:
1. A 2.0 kΩ variable resistor adjusted for a Forward Current ( $I_F$ ) of 10mA.
  2. Input pulse is adjusted so  $I_{R(peak)}$  is equal to 10mA.
  3.  $t_p \gg t_{rr}$

**Figure 1. Recovery Time Equivalent Test Circuit**

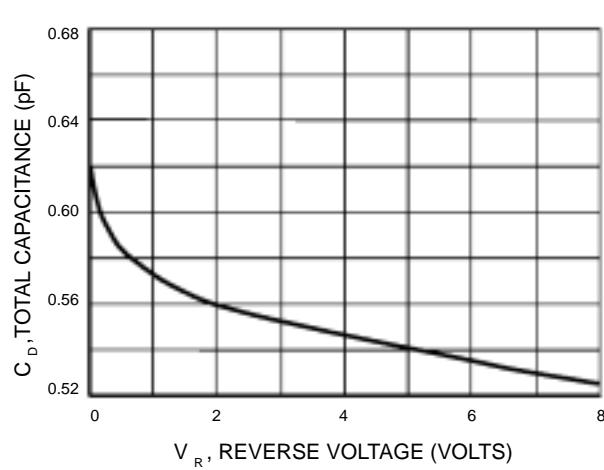
## CURVES APPLICABLE TO EACH DIODE



V<sub>F</sub>, FORWARD VOLTAGE (VOLTS)



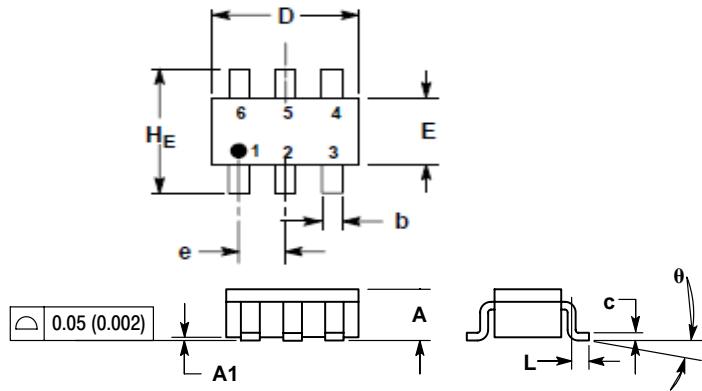
V<sub>R</sub>, REVERSE VOLTAGE (VOLTS)



**Figure 4. Capacitance**

# LIMN10T1G, S-LIMN10T1G

## TSOP-6



| DIM            | MILLIMETERS |      |      | INCHES |       |       |
|----------------|-------------|------|------|--------|-------|-------|
|                | MIN         | NOM  | MAX  | MIN    | NOM   | MAX   |
| A              | 0.90        | 1.00 | 1.10 | 0.035  | 0.039 | 0.043 |
| A1             | 0.01        | 0.06 | 0.10 | 0.001  | 0.002 | 0.004 |
| b              | 0.25        | 0.37 | 0.50 | 0.010  | 0.015 | 0.020 |
| c              | 0.10        | 0.18 | 0.26 | 0.004  | 0.007 | 0.010 |
| D              | 2.90        | 3.00 | 3.10 | 0.114  | 0.118 | 0.122 |
| E              | 1.30        | 1.50 | 1.70 | 0.051  | 0.059 | 0.067 |
| e              | 0.85        | 0.95 | 1.05 | 0.034  | 0.037 | 0.041 |
| L              | 0.20        | 0.40 | 0.60 | 0.008  | 0.016 | 0.024 |
| H <sub>E</sub> | 2.50        | 2.75 | 3.00 | 0.099  | 0.108 | 0.118 |
| θ              | 0°          | —    | 10°  | 0°     | —     | 10°   |

### SOLDERING FOOTPRINT\*

